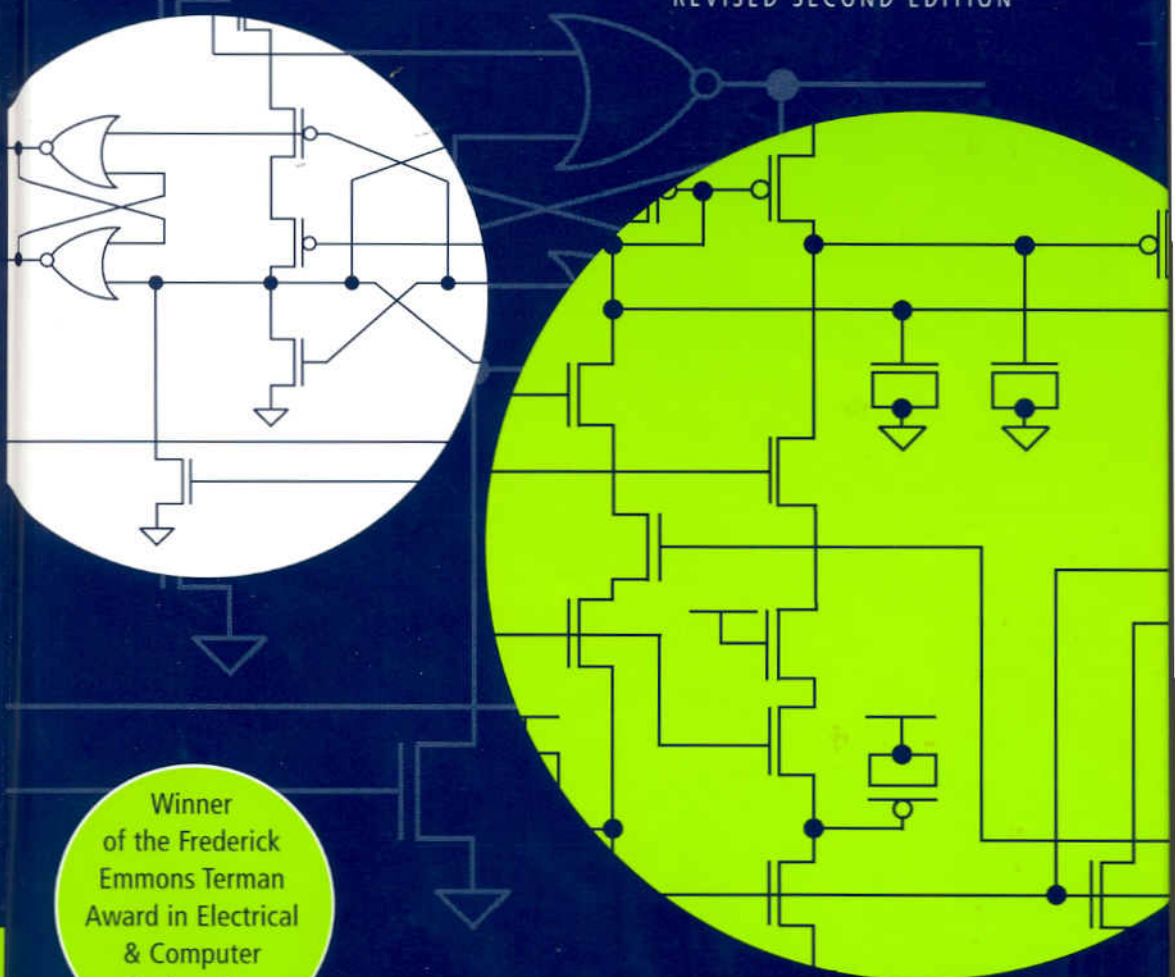
IEEE Press Series on Microelectronic Systems
Stuart K. Tewksbury and Joe E. Brewer, Series Editors

CMOS

CIRCUIT DESIGN, LAYOUT, AND SIMULATION

REVISED SECOND EDITION



Winner of the Frederick Emmons Terman Award in Electrical & Computer Engineering

R. JACOB BAKER

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